L Number	Hits	Search Text	DB	Time stamp
24	2	6713347.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/29 17:20
25	0	6713347.URPN.	USPAT	2004/10/29 17:18
26	18	("5182719" "5600164" "5663084" "5668035" "5768194" "5834352" "5861347" "5888869" "5910016" "5926729" "5989948" "6017797" "6087225" "6133164" "6165849" "6165918" "6228721" "6261978").PN.	USPAT	2004/10/29
27	12	(("5182719" "5600164" "5663084" "5668035" "5768194" "5834352" "5861347" "5888869" "5910016" "5926729" "5989948" "6017797" "6087225" "6133164" "6165849" "6165918" "6228721" "6261978").PN.) and (high adj voltage)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/29 17:20
28	7	((("5182719" "5600164" "5663084" "5668035" "5768194" "5834352" "5861347" "5888869" "5910016" "5926729" "5989948" "6017797" "6087225" "6133164" "6165849" "6165918" "6228721" "6261978").PN.) and (high adj voltage)) and (low adj	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/29 17:27
29	8279	form\$3 with first with ion with implant\$5 with layer	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/29 17:28
30	540	implant\$5 with high with voltage with well	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/29 18:12
31	7063	form\$3 with second with ion with implant\$5 with layer	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/29 17:29
32	2049	remov\$3 with second with first with ion with implant\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/29 17:29
33	24	(form\$3 with first with ion with implant\$5 with layer) and (implant\$5 with high with voltage with well) and (form\$3 with second with ion with implant\$5 with layer) and (remov\$3 with second with first with ion with implant\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/29 18:12
34	18	((form\$3 with first with ion with implant\$5 with layer) and (implant\$5 with high with voltage with well) and (form\$3 with second with ion with implant\$5 with layer) and (remov\$3 with second with first with ion with implant\$5)) and (@ad<20020222 or @rlad<20020222)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/29 18:13
35	320	implant\$5 with low with voltage with well	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/29 18:12
36	35	(form\$3 with first with ion with implant\$5 with layer) and (implant\$5 with high with voltage with well) and (form\$3 with second with ion with implant\$5 with layer) and (implant\$5 with low with voltage with well)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/29 18:12

37	22	((form\$3 with first with ion with implant\$5 with layer) and (implant\$5 with high with voltage with well) and (form\$3 with second with ion with implant\$5 with layer) and (implant\$5 with low with voltage with well)) and (@ad<20020222 or @rlad<20020222)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/29 18:13
38	17	(((form\$3 with first with ion with implant\$5 with layer) and (implant\$5 with high with voltage with well) and (form\$3 with second with ion with implant\$5 with layer) and (implant\$5 with low with voltage with well)) and (@ad<20020222 or @rlad<20020222)) not (((form\$3 with first with ion with implant\$5 with layer) and (implant\$5 with high with voltage with well) and (form\$3 with second with ion with implant\$5 with layer) and (remov\$3 with second with first with ion with implant\$5)) and (@ad<20020222 or @rlad<20020222))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/29 18:13
-	3203	438/22\$1.ccls. or 438/518.ccls. or 438/519.ccls. or 438/527.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/29 17:17
_	18	(438/22\$1.ccls. or 438/518.ccls. or 438/519.ccls. or 438/527.ccls.) and (high with voltage with (n adj well)) and (low with voltage with (p adj well))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/15 17:46
-	1	(sixth adj mask\$3) and (high with voltage with (n adj well)) and (low with voltage with (p adj well))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 11:21
_	70	(438/22\$1.ccls. or 438/518.ccls. or 438/519.ccls. or 438/527.ccls.) and (high with voltage with well) and (low with voltage with well)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/15 18:40
_	68	((438/22\$1.ccls. or 438/518.ccls. or 438/519.ccls. or 438/527.ccls.) and (high with voltage with well) and (low with voltage with well)) and (@ad<20020222 or @rlad<20020222)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/15 17:47
_	324	(high with voltage with well) and (first with low with voltage with well) and (second with low with voltage with well)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/15 19:55
-	39	<pre>((high with voltage with well) and (first with low with voltage with well) and (second with low with voltage with well)) and (implant\$5 with (p adj (body or region or well)))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/15 19:29
-	0	20030162375.URPN.	USPAT	2003/12/15 18:43
_	44	257/548.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/15 19:13
-		<pre>((high with voltage with well) and (first with low with voltage with well) and (second with low with voltage with well)) and (implant\$5 with p with high with voltage)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/15 19:29
_	7	((first with mask\$3) same (implant\$5 with high with voltage with well)) and ((second with mask\$3) same (first with low with voltage with well))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/15 19:57
-	2579	high with voltage with well with (implant\$5 or form\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 11:22

-	201	low with voltage with well with	USPAT;	2003/12/16
		(implant\$5 or form\$3) with first	US-PGPUB;	11:23
			EPO; JPO;	
_	196	low with voltage with well with	DERWENT USPAT;	2003/12/16
-	196	(implant\$5 or form\$3) with second	US-PGPUB;	11:23
		(Implantes of formes) with second	EPO; JPO;	11.23
			DERWENT	
-	114	(high with voltage with well with	USPAT;	2003/12/16
		(implant\$5 or form\$3)) and (low with	US-PGPUB;	11:23
		voltage with well with (implant\$5 or	EPO; JPO;	
		form\$3) with first) and (low with voltage	DERWENT	
		with well with (implant\$5 or form\$3) with		
	2000	second)	***	2002/12/16
_	3208	438/22\$1.ccls. or 438/518.ccls. or	USPAT; US-PGPUB;	2003/12/16
		438/519.ccls. or 438/527.ccls.	EPO; JPO;	11:24
			DERWENT	
_	11	((high with voltage with well with	USPAT;	2003/12/16
		(implant\$5 or form\$3)) and (low with	US-PGPUB;	12:52
		voltage with well with (implant\$5 or	EPO; JPO;	
		form\$3) with first) and (low with voltage	DERWENT	
		with well with (implant\$5 or form\$3) with		
		second)) and (438/22\$1.ccls. or		
		438/518.ccls. or 438/519.ccls. or		
	_	438/527.ccls.)	HCD2m.	2002/12/16
-	6	((high with voltage with well with	USPAT; US-PGPUB;	2003/12/16 12:42
		(implant\$5 or form\$3)) and (low with voltage with well with (implant\$5 or	EPO; JPO;	12:42
		form\$3) with first) and (low with voltage	DERWENT	
		with well with (implant\$5 or form\$3) with	<i>D S S S S S S S S S S</i>	
		second)) and cmos and dmos		
_	7	1	USPAT;	2003/12/16
		(implant\$5 or form\$3))) and (low with	US-PGPUB;	14:16
		voltage with well with (implant\$5 or	EPO; JPO;	
	_	form\$3) with first) and cmos and dmos	DERWENT	0000/10/16
-	8	((high with voltage with well with	USPAT;	2003/12/16
		(implant\$5 or form\$3)) and (low with voltage with well with (implant\$5 or	US-PGPUB; EPO; JPO;	14:16
		form\$3) with first) and (low with voltage	DERWENT	,
		with well with (implant\$5 or form\$3) with	7212	
		second)) and (fifth with mask\$3)		
 -	144		USPAT;	2003/12/16
		(implant\$5 or form\$3))) and (low with	US-PGPUB;	13:13
1		voltage with well with (implant\$5 or	EPO; JPO;	
		form\$3) with first)	DERWENT	0000/10/16
-	131	(((high with voltage with well with	USPAT;	2003/12/16 13:13
		(implant\$5 or form\$3))) and (low with voltage with well with (implant\$5 or	US-PGPUB; EPO; JPO;	13.13
		form\$3) with first)) and (@ad<20020222 or	DERWENT	
		Orlad<20020222)		,
_	1		USPAT;	2003/12/16
		(implant\$5 or form\$3)) and (low with	US-PGPUB:	19:53
1		voltage with well with (implant\$5 or	EPO; JPO;	
		form\$3) with first) and (low with voltage	DERWENT	,
		with well with (implant\$5 or form\$3) with		
	1	second)) and (fifth with photoresist with		
l_	1	film) ((high with voltage with well with	USPAT;	2003/12/16
-		(implant\$5 or form\$3))) and (low with	US-PGPUB;	19:55
		voltage with well with (implant\$5 or	EPO; JPO;	
		form\$3) with first) and photodiode and	DERWENT	
1		mems		
-	5	((high with voltage with well with	USPAT;	2003/12/16
	1	(implant\$5 or form\$3))) and (low with	US-PGPUB;	19:58
	1	voltage with well with (implant\$5 or	EPO; JPO;	
]	form\$3) with first) and photodiode	DERWENT	2002/12/16
-	21	((high with voltage with well with (implant\$5 or form\$3))) and (low with	USPAT; US-PGPUB;	2003/12/16
	1	(implants or formss))) and (low with voltage with well with (implant\$5 or	EPO; JPO;	19.33
		form\$3)) and photodiode	DERWENT	
			<u></u>	

_	1	((high with voltage with well with	USPAT;	2003/12/16
		(implant\$5 or form\$3))) and (low with	US-PGPUB;	20:04
		voltage with well with (implant\$5 or	EPO; JPO; DERWENT	,
1_	3	form\$3)) and photodiode and mems ((high with voltage with well with	USPAT;	2003/12/16
	5	(implant\$5 or form\$3))) and (low with	US-PGPUB;	20:3712710
		voltage with well with (implant\$5 or	EPO; JPO;	
		form\$3)) and mems	DERWENT	
-	21	(high with voltage with well) and (low	USPAT;	2003/12/16
		with voltage with well) and mems	US-PGPUB;	21:35
			EPO; JPO;	
	1	high adj voltage adj well) and (low adj	DERWENT USPAT;	2003/12/16
	1	voltage adj well) and mems	US-PGPUB;	20:11
		· · · · · · · · · · · · · · · · · · ·	EPO; JPO;	
			DERWENT	
_	2	cmos same dmos same mems	USPAT;	2003/12/16
			US-PGPUB;	21:04
		1	EPO; JPO;	
1_	10	cmos and dmos and mems	DERWENT USPAT;	2003/12/16
1 -		Chos and dhos and helis	US-PGPUB;	21:05
1 -			EPO; JPO;	
			DERWENT	_
-	2420	mem same (accelerometer or sensor)	USPAT;	2003/12/16
			US-PGPUB;	21:03
			EPO; JPO; DERWENT	
_	2420	mems same (accelerometer or sensor)	USPAT;	2003/12/16
	2420	ments same (accelerometer of sensor)	US-PGPUB;	21:03
			EPO; JPO;	
			DERWENT	
-	1862	mems with (accelerometer or sensor)	USPAT;	2003/12/16
			US-PGPUB;	21:03
			EPO; JPO; DERWENT	
1_	509	mems with accelerometer	USPAT;	2003/12/16
	303	memb with doctorous	US-PGPUB;	21:03
			EPO; JPO;	
			DERWENT	0000/10/16
-	2	cmos same dmos same photodiode	USPAT;	2003/12/16
			US-PGPUB; EPO; JPO;	
			DERWENT	
_	16	cmos and dmos and photodiode	USPAT;	2003/12/16
i		•	US-PGPUB;	21:05
			EPO; JPO;	
			DERWENT USPAT;	2003/12/16
-	31	cmos same dmos same soi	USPAT; US-PGPUB;	21:18
			EPO; JPO;	
		·	DERWENT	
-	2	5578506.pn.	USPAT;	2003/12/16
			US-PGPUB;	21:30
			EPO; JPO; DERWENT	
_	2	5681761.pn.	USPAT;	2003/12/16
		0001/01.pii.	US-PGPUB;	21:30
			EPO; JPO;	
			DERWENT	
-	113		USPAT;	2003/12/16
	1	with voltage with well) and photodiode	US-PGPUB;	21:36
			EPO; JPO; DERWENT	
-	104	((high with voltage with well) and (low	USPAT;	2003/12/16
		with voltage with well) and photodiode)	US-PGPUB;	21:47
		and @ad<20020222	EPO; JPO;	
	_		DERWENT	2002/12/26
1-	1	(high adj voltage adj well) and (low adj voltage adj well) and photodiode	USPAT; US-PGPUB;	2003/12/16 21:37
		voltage adj well; and photodrode	EPO; JPO;	21.37
			DERWENT	
		1		

	71006		110 D D M .	1 2002 (12 (16
-	71986	photodiode	USPAT;	2003/12/16
			US-PGPUB;	21:48
			EPO; JPO;	
		, , , , , , , , , , , , , , , , , , , ,	DERWENT	0000 (10 (16
-	67	photodiode and dmos	USPAT;	2003/12/16
	1	,	US-PGPUB;	21:48
			EPO; JPO;	
·			DERWENT	
-	35	(implant\$5 with high with voltage with	USPAT;	2004/10/25
		well) and (implant\$5 with low with	US-PGPUB;	17:04
		voltage with well) and (first adj mask)	EPO; JPO;	
		and (second adj mask)	DERWENT	
-	28	(implant\$5 with high with voltage with	USPAT;	2004/10/25
		well) and (implant\$5 with low with	US-PGPUB;	17:07
		voltage with well) and (first adj mask)	EPO; JPO;	:
		and (second adj mask) and (@ad<20020222	DERWENT	
İ		or @rlad<20020222)		
-	0	((implant\$5 with high with voltage with	USPAT;	2004/06/29
		well) same (first adj protective)) and	US-PGPUB;	14:23
		((implant\$5 with low with voltage with	EPO; JPO;	
		well) same(second adj protective)) and	DERWENT	
		(@ad<20020222 or @rlad<20020222)		
-	0	((implant\$5 with high with voltage with	USPAT;	2004/06/29
		well) same (first adj oxide)) and	US-PGPUB;	14:23
		((implant\$5 with low with voltage with	EPO; JPO;	
		well) same(second adj oxide)) and	DERWENT	
		(@ad<20020222 or @rlad<20020222)		
_	l 0	((implant\$5 with high with voltage with	USPAT;	2004/06/29
		well) same (first with protective)) and	US-PGPUB;	15:48
}		((implant\$5 with low with voltage with	EPO; JPO;	
		well) same (second with protective)) and	DERWENT	
		(@ad<20020222 or @rlad<20020222)		
_	8	((implant\$5 with high with voltage with	USPAT;	2004/06/29
		well) same (first with oxide)) and	US-PGPUB;	14:41
		((implant\$5 with low with voltage with	EPO; JPO;	i I
		well) same(second with oxide)) and	DERWENT	
		(@ad<20020222 or @rlad<20020222)		•
_	152	((implant\$5 with high with voltage with	USPAT;	2004/06/29
		well) same (implant\$5 with low with	US-PGPUB;	14:28
		voltage with well)) and (@ad<20020222 or	EPO; JPO;	
		@rlad<20020222)	DERWENT	
_	77	1 ⁻	USPAT;	2004/06/29
		well) same (implant\$5 with low with	US-PGPUB;	14:28
	1	voltage with well)) and (@ad<20020222 or	EPO; JPO;	
	1	@rlad<20020222)) and 438/\$3.ccls.	DERWENT]
_	7	1	USPAT;	2004/06/29
	1	well with first with mask) and (implant\$5	US-PGPUB;	14:42
		with low with voltage with well with	EPO; JPO;	
		second with mask) and (@ad<20020222 or	DERWENT	
	1	@rlad<20020222)		
_	3	((high with voltage with well) same	USPAT;	2004/06/29
	'	(first with protective)) and ((low with	US-PGPUB;	15:50
		voltage with well) same (second with	EPO; JPO;	
		protective)) and (@ad<20020222 or	DERWENT	
		@rlad<20020222)		
- \	18	((high with voltage with well) same	USPAT;	2004/06/29
		(first with mask)) and ((low with voltage	US-PGPUB;	16:46
		with well) same (second with mask)) and	EPO; JPO;	
	Ī	(@ad<20020222 or @rlad<20020222)	DERWENT	
]_	30	((high with voltage with well) same	USPAT;	2004/06/29
		(first with oxide)) and ((low with	US-PGPUB;	17:38
	1	voltage with well) same (second with	EPO; JPO;	
	1	oxide)) and (@ad<20020222 or	DERWENT	
		@rlad<20020222)		
l _	54	1	USPAT;	2004/10/25
1		(first with mask)) and ((low with voltage	US-PGPUB;	17:37
		with implant\$5) same (second with mask))	EPO; JPO;	- 1 . 3 .
		and (@ad<20020222 or @rlad<20020222)	DERWENT	
		I wild (Cadillottell of Giladillottel)	1 221/11/21/41	

-	0	(implant\$5 with high with voltage with	USPAT;	2004/06/29
		well) and ((low with voltage with well)	US-PGPUB;	17:40
		same (remov\$3 with second with portion	EPO; JPO;	
		with first with mask)) and (@ad<20020222	DERWENT	
		or @rlad<20020222)		
-	44	(high with voltage with well) and (low	USPAT;	2004/06/29
		with voltage with well) and (remov\$3 with	US-PGPUB;	18:16
İ		second with portion with first with mask)	EPO; JPO;	
		and (@ad<20020222 or @rlad<20020222)	DERWENT	
-	867	(438/200.ccls. or 438/279.ccls.) and	USPAT;	2004/06/29
		(@ad<20020222 or @rlad<20020222)	US-PGPUB;	18:17
			EPO; JPO;	
-			DERWENT	
-	205	((438/200.ccls. or 438/279.ccls.) and	USPAT;	2004/06/29
		(@ad<20020222 or @rlad<20020222)) and	US-PGPUB;	18:17
		(high with voltage) and (low with	EPO; JPO;	
	150	voltage)	DERWENT	0004/06/00
-	159		USPAT;	2004/06/29
		(@ad<20020222 or @rlad<20020222)) and	US-PGPUB;	18:18
		(high with voltage) and (low with	EPO; JPO;	
		voltage)) and mask\$3	DERWENT	2004/07/12
-	0	wo200237547	USPAT;	10:56
			US-PGPUB; EPO; JPO;	10.30
			DERWENT	
_	1	"wo 200237547"	USPAT;	2004/07/12
-	1	WO 200231341	US-PGPUB;	10:58
			EPO; JPO;	20100
			DERWENT	
_	4	985447.ap.	USPAT;	2004/07/12
	1		US-PGPUB;	10:58
	ł		EPO; JPO;	
	1		DERWENT	
_	8	(implant\$5 with (high adj voltage adj	USPAT;	2004/10/25
		well)) and (implant\$5 with (low adj	US-PGPUB;	20:05
		voltage adj well))	EPO; JPO;	
			DERWENT	
-	4		USPAT;	2004/10/25
		well)) and (implant\$5 with (low adj	US-PGPUB;	17:10
		voltage adj well))) and (@ad<20020222 or	EPO; JPO;	
	1.0	@rlad<20020222)	DERWENT	2004/10/25
-	10	(implant\$5 same (high adj voltage adj	USPAT;	17:09
1		well)) and (implant\$5 same (low adj voltage adj well))	US-PGPUB; EPO; JPO;	11.09
		vortage auj weil)	DERWENT	
l _	6	((implant\$5 same (high adj voltage adj	USPAT;	2004/10/25
	1	well)) and (implant\$5 same (low adj	US-PGPUB;	17:15
		voltage adj well))) and (@ad<20020222 or	EPO; JPO;	,
	1	@rlad<20020222)	DERWENT	·
-	2	I .	USPAT;	2004/10/25
		well)) and (implant\$5 same (low adj	US-PGPUB;	17:10
		voltage adj well))) and (@ad<20020222 or	EPO; JPO;	
		@rlad<20020222)) not (((implant\$5 with	DERWENT	
		(high adj voltage adj well)) and		
		(implant\$5 with (low adj voltage adj		
}		well))) and (@ad<20020222 or		
l .		@rlad<20020222))		2004/10/25
-	26	(high adj voltage adj well) same (low adj	USPAT;	2004/10/25
		voltage adj well)	US-PGPUB;	17:23
			EPO; JPO;	
I _	20	//high add woltage add well) game /ler-	DERWENT USPAT;	2004/10/25
-	20	((high adj voltage adj well) same (low adj voltage adj well)) and (@ad<20020222	US-PGPUB;	20:14
		or @rlad<20020222)	EPO; JPO;	
		or craw.royavaaa,	DERWENT	
-	27	(high adj voltage adj well) and (low adj	USPAT;	2004/10/25
]	voltage adj well) and implant\$5	US-PGPUB;	17:23
			EPO; JPO;	
	1		DERWENT	

Page 6

-	21	((high adj voltage adj well) and (low adj	USPAT;	2004/10/25
		voltage adj well) and implant\$5) and	US-PGPUB;	17:24
		(@ad<20020222 or @rlad<20020222)	EPO; JPO;	
			DERWENT	
-	8	(((high adj voltage adj well) and (low	USPAT;	2004/10/25
		adj voltage adj well) and implant\$5) and	US-PGPUB;	17:24
	1	(@ad<20020222 or @rlad<20020222)) not	EPO; JPO;	
		(((high adj voltage adj well) same (low	DERWENT	
		adj voltage adj well)) and (@ad<20020222		
		or @rlad<20020222))		
_	58	((high with voltage with implant\$5) same	USPAT;	2004/10/25
		(first with mask\$3)) and ((low with	US-PGPUB;	20:00
		voltage with implant\$5) same (second with	EPO; JPO;	
		mask\$3)) and (@ad<20020222 or	DERWENT	1
		@rlad<20020222)		
_	58		USPAT;	2004/10/25
		(first with mask\$3)) and ((low with	US-PGPUB;	17:38
		voltage with implant\$5) same (second with	EPO; JPO;	
		mask\$3)) and (@ad<20020222 or	DERWENT	
		@rlad<20020222)) not (((high adj voltage		
		adj well) and (low adj voltage adj well)		
		and implant\$5) and (@ad<20020222 or		
		@rlad<20020222))		
_	13	((high with voltage) same implant\$5 same	USPAT;	2004/10/25
		(low with voltage) same (partial\$2 with	US-PGPUB;	20:01
		mask\$3)) and (@ad<20020222 or	EPO; JPO;	
		@rlad<20020222)	DERWENT	
_	541		USPAT;	2004/10/25
		(implant\$5 with (low adj voltage))	US-PGPUB;	20:12
		(EPO; JPO;	
			DERWENT	
_	212	((implant\$5 with (high adj voltage)) same	USPAT;	2004/10/25
		mask\$3) and ((implant\$5 with (low adj	US-PGPUB;	20:14
		voltage)) same mask\$3)	EPO; JPO;	
		1	DERWENT	
_	135	(((implant\$5 with (high adj voltage))	USPAT;	2004/10/25
		same mask\$3) and ((implant\$5 with (low	US-PGPUB;	20:14
		adj voltage)) same mask\$3)) and	EPO; JPO;	
		438/\$3.ccls.	DERWENT	
_	119	((((implant\$5 with (high adj voltage))	USPAT;	2004/10/29
		same mask\$3) and ((implant\$5 with (low	US-PGPUB;	17:30
		adj voltage)) same mask\$3)) and	EPO; JPO;	
		438/\$3.ccls.) and (@ad<20020222 or	DERWENT	
		@rlad<20020222)		